

V.P. & R.P.T.P SCIENCE COLLEGE
INTERANAL EXAM
T.Y.B.Sc (6th semester.) ELECTRONICS
Time : 11.00 a.m. to 12.30 p.m.

(25 Marks)

SUB. CODE:-US06CELE02

DATE:-13/03/2018

Q-1 Choose correct answer

[3]

1. BJT memory is _____ Mos memory.
(A) faster (C) slower
(B) veryslow (D) none of above
2. Tristate switch has low and high & _____ state.
(A) Floating (C) Short Circuit
(B) Open (D) none of above
3. D/A Convert are part of _____ converter
(A) A/D (C) D/D
(B) A/A (D) none of above



Q-2 Short answer type question.(attempt any two)

[4]

1. Draw the circuit of weighted resistor type DAC.
2. Draw the figure single transistor dynamic memory cell.
3. Explain what do you understand by Program memory and Data memory.

Q-3 Draw a neat circuit of R-2R ladder type DAC and explain its working for any two of the following input.

[6]

(1) 1000 (2) 0100 (3) 0101 (4) 0001

OR

Q-3 Give an account of counter type A/D converter.

[6]

Q-4 Give an account of MASK programmed ROM.

[6]

OR

Q-4 Give an account of programmable Read only memory.

[6]

Q-5 Write a note RAM, ROM and PROM.

[6]

OR

- Q-5**
- (A) Explain in detail ROM organization drawing block diagram.
 - (B) Explain ROM diagram in detail.

[6]
